SCHOTTKY BARRIER DIODES

FEATURES :

* For general purpose applications
* The SD103 series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
* The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
* These diodes are also available in the MiniMELF case with type designations LL103A thru LL103C.

Maximum Ratings and Thermal Characteristics (T_C = 25 °C unless otherwise noted)

		Symbol	Value	Unit
	SD103AWS		40	
	SD103BWS		30	
	SD103CWS		20	
Maximum Single Cycle Surge 10 µs Square Wave		I_{FSM}	2	A
Power Dissipation (Infinite Heat Sink)		P_{tot}	150(1)	mW
Thermal Resistance Junction to Ambient Air		$R_{\theta JA}$	650(1)	°C/W
Junction Temperature		T_J	125(1)	°C
Storage temperature range		T_{STG}	-55 to + 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Min	Typ	Max	Unit

RATING AND CHARACTERISTIC CURVES (SD103AWS - SD103CWS)

Typical variation of forward current vs. forward voltage for primary conduction through the schottky barrier

Typical high current forward conduction curve